ABSTRACT OF THE DISCLOSURE

A semiconductor device having a trench isolation includes a trench formed in a surface of a semiconductor substrate and a buried insulating layer which fills the inside of the trench and has its top surface entirely located above the surface of the semiconductor substrate. A part of the buried insulating layer that protrudes from the surface of the semiconductor substrate has a projecting portion which is located on the surface of the semiconductor substrate and projects outward from a region directly above the trench. The projecting portion has a structure formed of at least two stacked insulating layers. Accordingly, the semiconductor device having the trench isolation can be provided by which a reverse narrow-channel effect can be suppressed and a reliable gate insulating layer can be obtained.